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(54) **Title:** METHOD FOR FABRICATION OF FINE-FEATURED ETCH MASK USING DIRECT ATOMIC LAYER PROCESSING

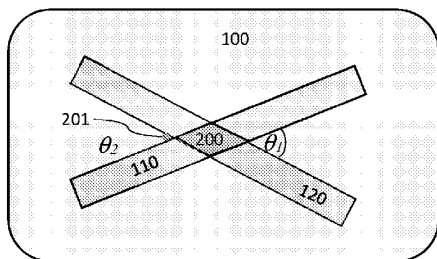


FIG. 4A

(57) **Abstract:** The disclosure relates to systems and methods for forming etch masks using direct atomic layer processing. Specifically, the disclosure relates to methods of forming etch masks having fine features at the substrate level, using microreactor direct atomic layer processing (μ DALP).

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